NSN 5961-00-072-8573

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View Online at https://aerobasegroup.com/nsn/5961-00-072-8573 **Inclosure Material:** Metal **Overall Length:** Between 0.300 inches and 0.400 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.424 inches and 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 75.0 breakdown voltage, emitter-to-base, collector open and 10.0 peak negative gate voltage and 50.0 reverse voltage, peak **Current Rating Per Characteristic:** 2.00 amperes forward current, total rms blank and 4.70 amperes forward current, total rms megahertz and 60.00 amperes forward current, total rms watts **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Special Features:** Must meet all test requirements of westinghouse dwg 58or299; junction pattern arrangement: npnp **Test Data Document:** 97942-580r299 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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